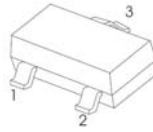


# LGE2302

N-Channel 20-V(D-S) Mosfet



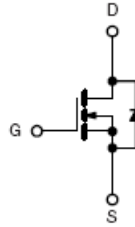
1. GATE
2. SOURCE
3. DRAIN

## Features

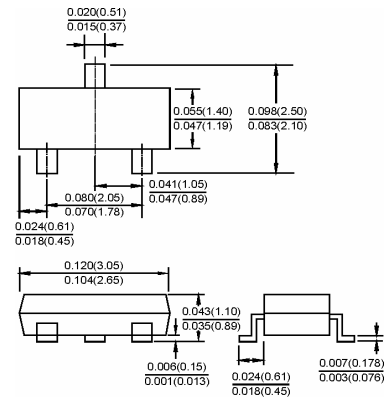
TrenchFET Power MOSFET

## Applications

- Load Switch for Portable Devices
- DC/DC Converter



## SOT-23



Dimensions in inches and (millimeters)

MARKING: 2302

## Maximum ratings ( $T_a=25^{\circ}\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	$V_{DS}$	20	V
Gate-Source Voltage	$V_{GS}$	$\pm 8$	
Continuous Drain Current	$I_D$	2.1	A
Continuous Source-Drain Current(Diode Conduction)	$I_S$	0.6	
Power Dissipation	$P_D$	0.35	W
Thermal Resistance from Junction to Ambient ( $t \leq 5s$ )	$R_{\theta JA}$	357	$^{\circ}\text{C}/\text{W}$
Operating Junction	$T_J$	150	$^{\circ}\text{C}$
Storage Temperature	$T_{STG}$	-55 ~ +150	

# LGE2302

N-Channel 20-V(D-S) Mosfet



## Electrical characteristics (T<sub>a</sub>=25°C unless otherwise noted)

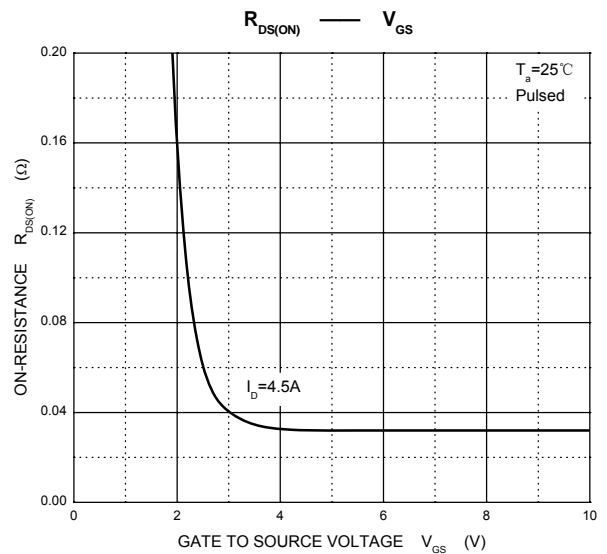
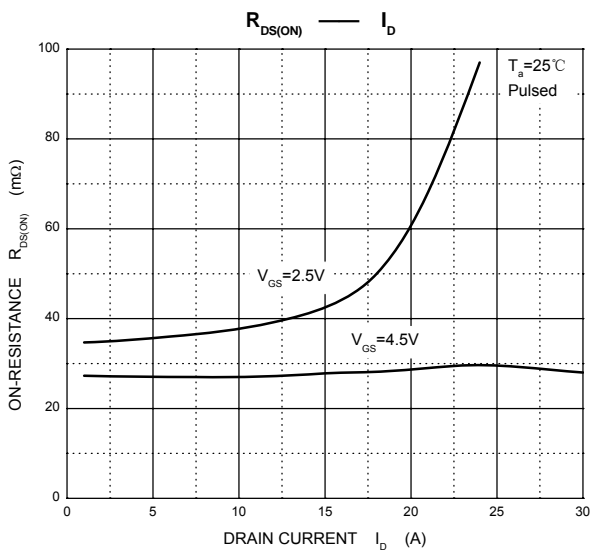
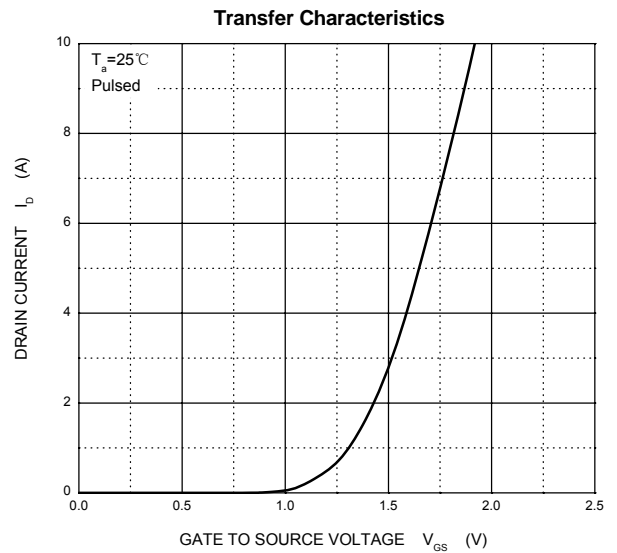
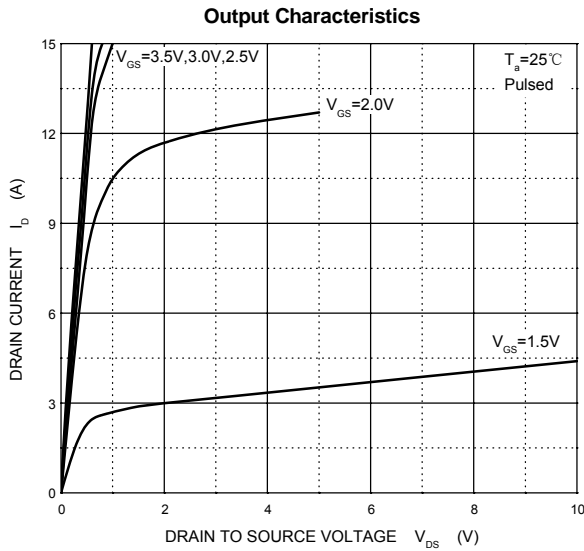
Parameter	Symbol	Test Condition	Min	Typ	Max	Units
<b>Static</b>						
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	V <sub>GS</sub> = 0V, I <sub>D</sub> = 10μA	20			V
Gate-threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 50μA	0.65	0.95	1.2	
Gate-body leakage	I <sub>GSS</sub>	V <sub>DS</sub> = 0V, V <sub>GS</sub> = ±8V			±100	nA
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>DS</sub> = 20V, V <sub>GS</sub> = 0V			1	μA
Drain-source on-resistance <sup>a</sup>	r <sub>DS(on)</sub>	V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		0.045	0.060	Ω
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 3.1A		0.070	0.115	
Forward transconductance <sup>a</sup>	g <sub>fs</sub>	V <sub>DS</sub> = 5V, I <sub>D</sub> = 3.6A		8		S
Diode forward voltage	V <sub>SD</sub>	I <sub>S</sub> = 0.94A, V <sub>GS</sub> = 0V		0.76	1.2	V
<b>Dynamic</b>						
Total gate charge	Q <sub>g</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 4.5V, I <sub>D</sub> = 3.6A		4.0	10	nC
Gate-source charge	Q <sub>gs</sub>			0.65		
Gate-drain charge	Q <sub>gd</sub>			1.5		
Input capacitance <sup>b</sup>	C <sub>iss</sub>	V <sub>DS</sub> = 10V, V <sub>GS</sub> = 0V, f = 1MHz		300		pF
Output capacitance <sup>b</sup>	C <sub>oss</sub>			120		
Reverse transfer capacitance <sup>b</sup>	C <sub>rss</sub>			80		
<b>Switching<sup>b</sup></b>						
Turn-on delay time	t <sub>d(on)</sub>	V <sub>DD</sub> = 10V, R <sub>L</sub> = 5.5Ω, I <sub>D</sub> ≈ 3.6A, V <sub>GEN</sub> = 4.5V, R <sub>g</sub> = 6Ω		7	15	ns
Rise time	t <sub>r</sub>			55	80	
Turn-off delay time	t <sub>d(off)</sub>			16	60	
Fall time	t <sub>f</sub>			10	25	

### Notes :

- Pulse Test : Pulse width ≤ 300μs, duty cycle ≤ 2%.
- These parameters have no way to verify.



## Typical Characteristics



# X-ON Electronics

Largest Supplier of Electrical and Electronic Components

*Click to view similar products for [MOSFET](#) category:*

*Click to view products by [Luguang](#) manufacturer:*

Other Similar products are found below :

[614233C](#) [648584F](#) [D2003UK](#) [705463DB](#) [MCH6422-TL-E](#) [FW231A-TL-E](#) [APT5010JFLL](#) [NTNS3A92PZT5G](#) [IRF100S201](#) [JANTX2N5237](#)  
[2SK2464-TL-E](#) [2SK3818-DL-E](#) [FCA20N60\\_F109](#) [FDZ595PZ](#) [STD6600NT4G](#) [FQD4P40TM\\_AM002](#) [FSS804-TL-E](#) [FW217A-TL-2W](#)  
[APT10050JVFR](#) [2SJ277-DL-E](#) [2SK1691-DL-E](#) [2SK2545\(Q,T\)](#) [D1014UK](#) [D2294UK](#) [405094E](#) [423220D](#) [MCH6646-TL-E](#) [TPCC8103,L1Q\(CM](#)  
[IRF3710](#) [367-8430-0972-503](#) [VN1206L](#) [424134F](#) [026935X](#) [051075F](#) [SBVS138LT1G](#) [614234A](#) [715780A](#) [NTNS3166NZT5G](#) [751625C](#) [873612G](#)  
[IPS70R2K0CEAKMA1](#) [APT8015JVFR](#) [APT50M85JVR](#) [APT5010JVFR](#) [APT12031JFLL](#) [APT12040JVR](#) [NTE6400](#) [NVC3S5A51PLZT1G](#)  
[JANTX2N6796U](#) [JANTX2N6784U](#)